

SILICON POWER TRANSISTOR 2SC4552

NPN SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SC4552 is a power transistor developed for high-speed switching and features low $V_{CE(sat)}$ and high h_{FE} . This transistor is ideal for use in drivers such as DC/DC converters and actuators.

In addition, a small resin-molded insulation type package contributes to high-density mounting and reduction of mounting cost.

FEATURES

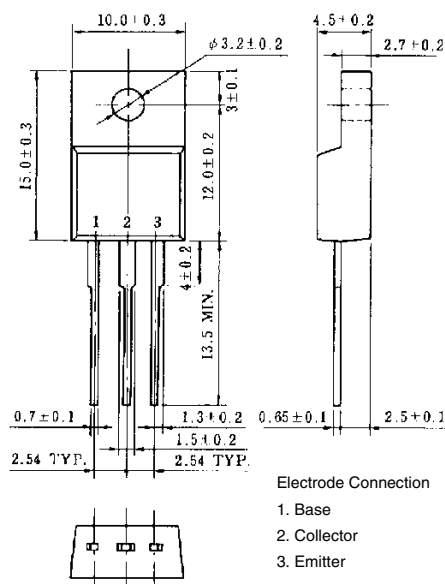
- High h_{FE} and low $V_{CE(sat)}$:
 $h_{FE} \geq 100$ ($V_{CE} = 2\text{ V}$, $I_C = 3\text{ A}$)
 $V_{CE(sat)} \leq 0.3\text{ V}$ ($I_C = 8\text{ A}$, $I_B = 0.4\text{ A}$)
- Mold package that does not require an insulating board or insulation bushing

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	60	V
Emitter to base voltage	V_{EBO}	7.0	V
Collector current (DC)	$I_{C(DC)}$	15	A
Collector current (pulse)	$I_{C(pulse)}^*$	30	A
Base current (DC)	$I_{B(DC)}$	7.5	A
Total power dissipation	P_T ($T_c = 25^\circ\text{C}$)	30	W
Total power dissipation	P_T ($T_a = 25^\circ\text{C}$)	2.0	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 10\%$

PACKAGE DRAWING (UNIT: mm)



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

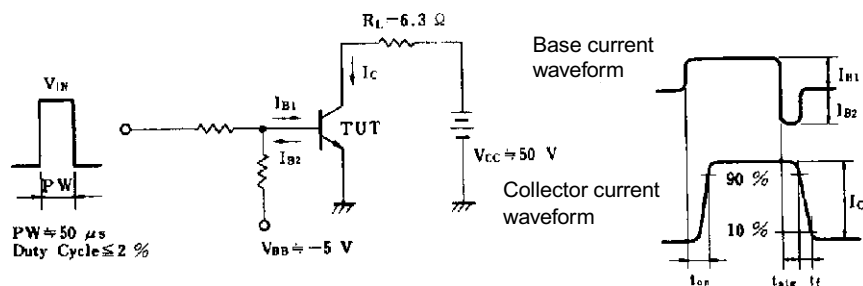
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	$V_{CE0(SUS)}$	$I_C = 8.0\text{ A}$, $I_B = 0.8\text{ A}$, $L = 1\text{ mH}$	60			V
Collector to emitter voltage	$V_{CEX(SUS)}$	$I_C = 8.0\text{ A}$, $I_{B1} = -I_{B2} = 0.8\text{ A}$, $V_{BE(OFF)} = -1.5\text{ V}$, $L = 180\text{ }\mu\text{H}$, clamped	60			V
Collector cutoff current	I_{CBO}	$V_{CB} = 60\text{ V}$, $I_E = 0$			10	μA
Collector cutoff current	I_{CER}	$V_{CE} = 60\text{ V}$, $R_{BE} = 50\text{ }\Omega$, $T_a = 125^\circ\text{C}$			1.0	mA
Collector cutoff current	I_{CEX1}	$V_{CE} = 60\text{ V}$, $V_{BE(OFF)} = -1.5\text{ V}$			10	μA
Collector cutoff current	I_{CEX2}	$V_{CE} = 60\text{ V}$, $V_{BE(OFF)} = -1.5\text{ V}$, $T_a = 125^\circ\text{C}$			1.0	mA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5.0\text{ V}$, $I_C = 0$			10	μA
DC current gain	h_{FE1}^*	$V_{CE} = 2.0\text{ V}$, $I_C = 1.5\text{ A}$	100			
DC current gain	h_{FE2}^*	$V_{CE} = 2.0\text{ V}$, $I_C = 3.0\text{ A}$	100		400	
DC current gain	h_{FE3}^*	$V_{CE} = 2.0\text{ V}$, $I_C = 8.0\text{ A}$	60			
Collector saturation voltage	$V_{CE(sat)1}^*$	$I_C = 8.0\text{ A}$, $I_B = 0.4\text{ A}$			0.3	V
Collector saturation voltage	$V_{CE(sat)2}^*$	$I_C = 12\text{ A}$, $I_B = 0.6\text{ A}$			0.5	V
Base saturation voltage	$V_{BE(sat)1}^*$	$I_C = 8.0\text{ A}$, $I_B = 0.4\text{ A}$			1.2	V
Base saturation voltage	$V_{BE(sat)2}^*$	$I_C = 12\text{ A}$, $I_B = 0.6\text{ A}$			1.5	V
Collector capacitance	C_{ob}	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1.0\text{ MHz}$		180		pF
Gain bandwidth product	f_T	$V_{CE} = 10\text{ V}$, $I_C = 1.5\text{ A}$		120		MHz
Turn-on time	t_{on}	$I_C = 8.0\text{ A}$, $R_L = 6.3\text{ }\Omega$, $I_{B1} = -I_{B2} = 0.4\text{ A}$, $V_{CC} \cong 50\text{ V}$ Refer to the test circuit.			0.3	μs
Storage time	t_{stg}				1.5	μs
Fall time	t_f				0.3	μs

* Pulse test $PW \leq 350\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

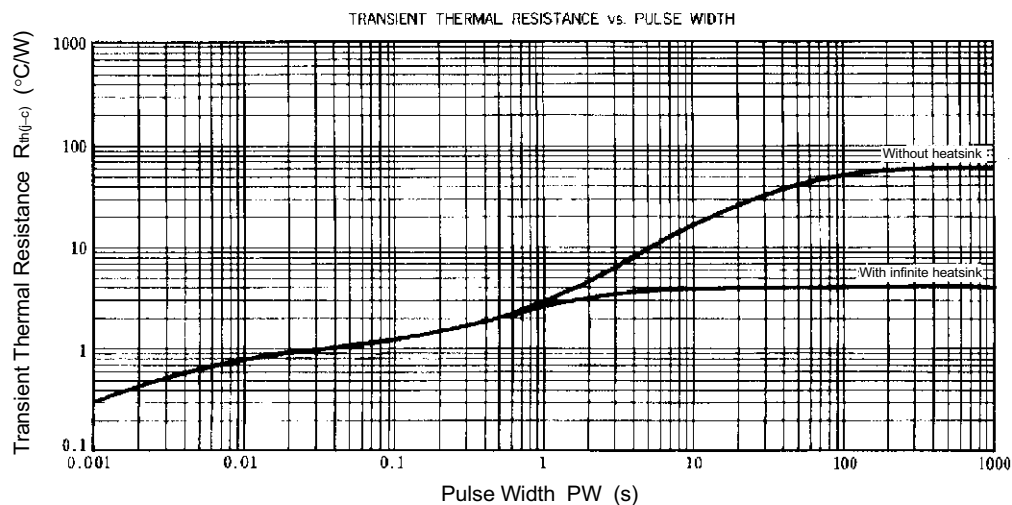
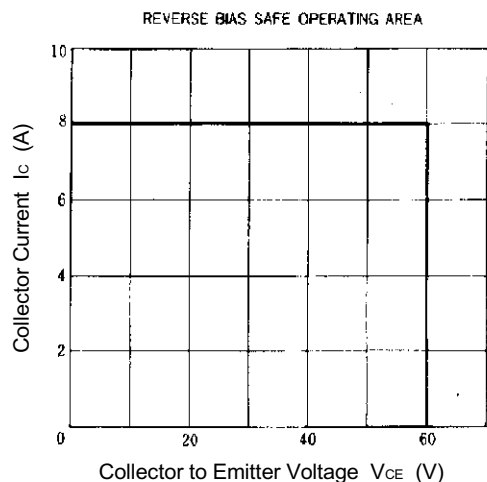
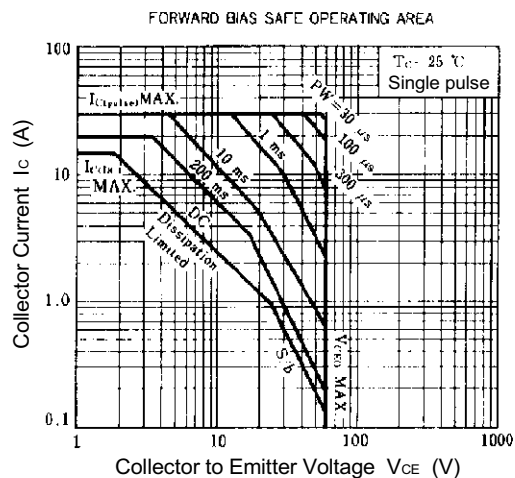
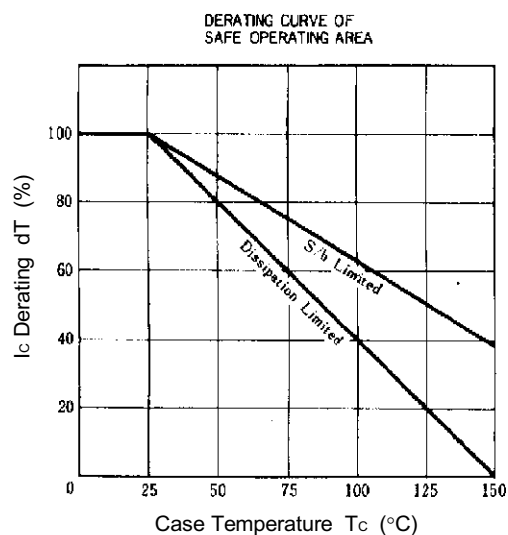
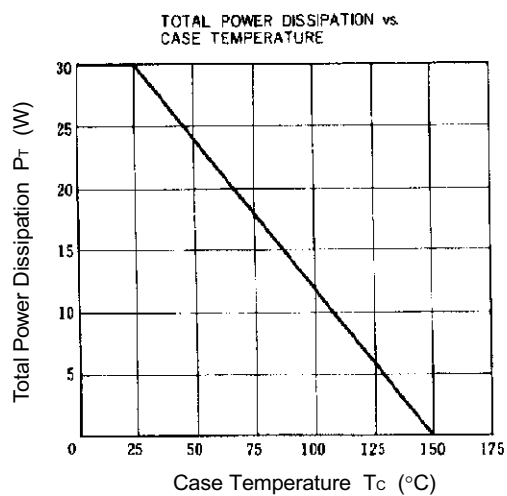
h_{FE} CLASSIFICATION

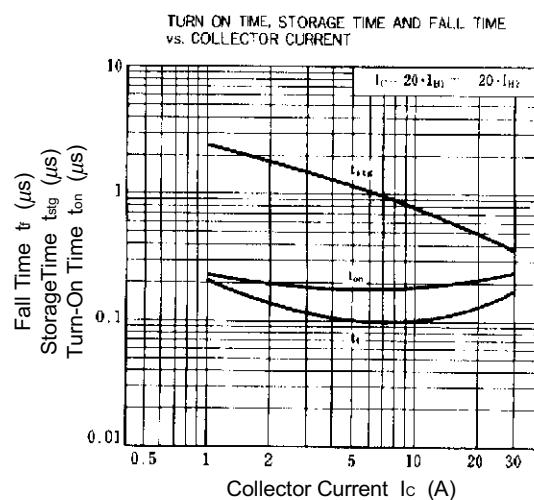
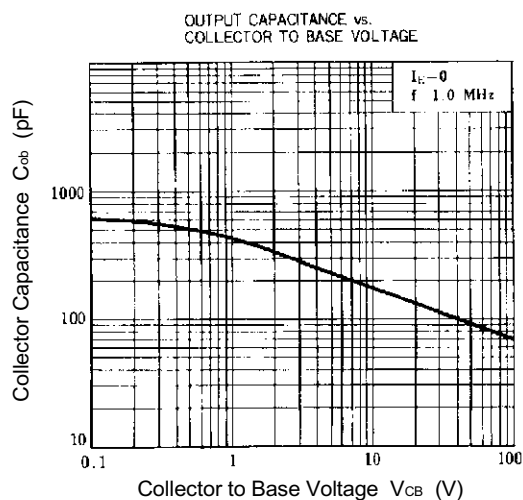
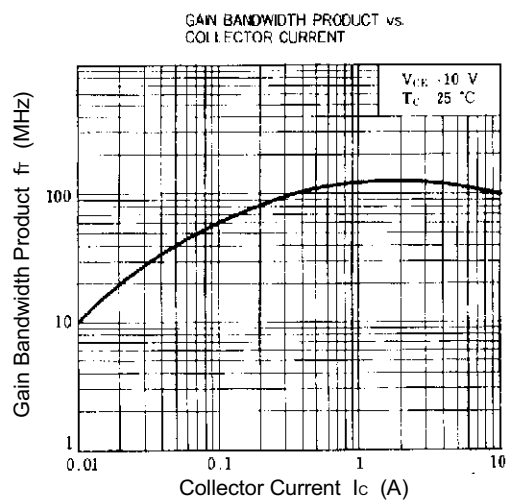
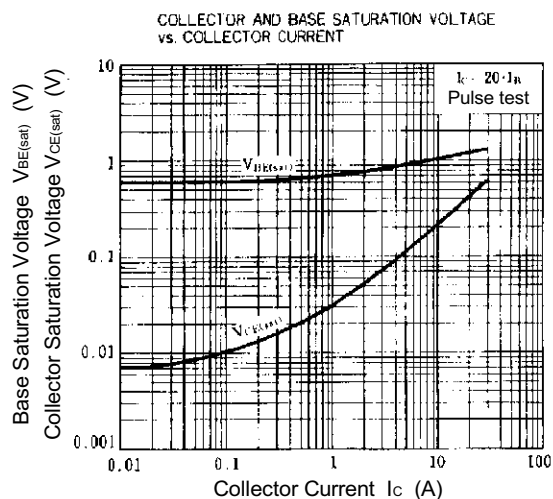
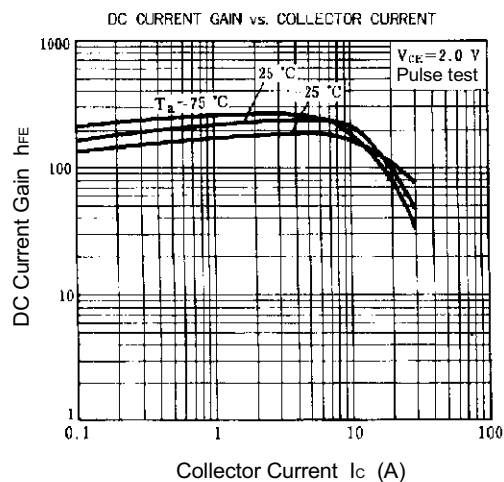
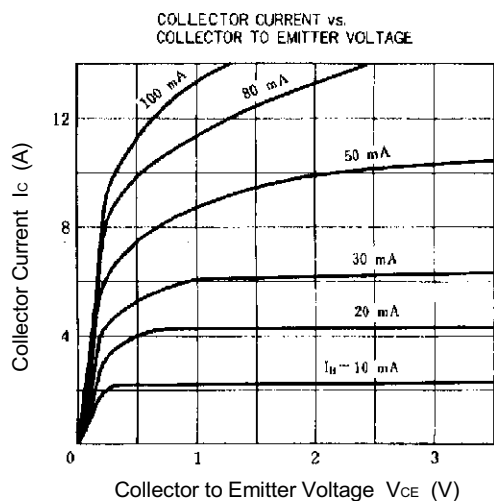
Marking	M	L	K
h_{FE2}	100 to 200	150 to 300	200 to 400

SWITCHING TIME (t_{on} , t_{stg} , t_f) TEST CIRCUIT



TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)





[MEMO]

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